TOSHIBA

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT MULTI CHIP

T D 6 2 M 8 6 0 4 A F

8ch LOW SATURATION VOLTAGE SOURCE DRIVER

The TD62M8604AF is Multi Chip IC incorporates 8 low saturation discrete (PNP : 2SA1680) transistors. This IC is suitable for a battery use motor drive and LED display module applications.

FEATURES

- Suitable for Motor drive circuit and LED display module
- Low Saturation Voltage

 $V_{CE(sat)} = -0.5V$ (Typ.) at $I_{C} = -0.5A$ $V_{BE (sat)} = -1.2V$ (Max.) at $I_{C} = -1.0A$

HSOP16 power small package sealed

BLOCK DIAGRAM



Weight : 0.50g (Typ.)



PIN CONNECTION (TOP VIEW)

IN1 [1	16] IN8
ουτ1 [2	15] OUT8
IN2 [3	14] IN7
ουτ2 [4	13] Ουτ7
vcc			Vcc
ουτ3 [5	12] OUT6
IN3 [6	11] IN6
00т4 [7	10] OUT5
IN4 [8	9	IN5

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MAXIMUM RATINGS (Ta = 25° C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage	Vcc	- 50	V	
Breakdown Voltage	V _{CBO}	- 60	V	
Breakdown Voltage	VCEO	- 50	V	
Breakdown Voltage	V _{EBO}	- 6	V	
Output Current	lo	- 2	A / ch	
Base Current	۱ _B	- 0.2	А	
Power Dissipation	PD	900	mW	
Junction Temperature	Tj	150	°C	
Operating Temperature	T _{opr}	- 40~85	°C	
Storage Temperature	T _{stg}	- 55~150	°C	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h _{FE} (1)	_	$V_{CE} = -2V, I_C = -0.1A$	120		400	
	h _{FE} (2)		$V_{CE} = -2V$, $I_C = -1.5A$	40			
Saturation Voltage	VCE (sat)	-	I _C = – 1A, I _B = – 50mA		_	- 0.5	V
	V _{BE} (sat)	—	I _C = – 1A, I _B = – 50mA	_	—	- 1.2	v
Transition Frequency	fT	_	$V_{CE} = -2V, I_{C} = -0.1A$	_	100		MHz
Leakage Current	lol	_	V _{CC} = - 50V		0	- 5	μA



PRECAUTIONS for USING

Utmost care is necessary in the design of the output line, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

OUTLINE DRAWING HSOP16-P-300-1.00





Weight : 0.50g (Typ.)

Unit : mm